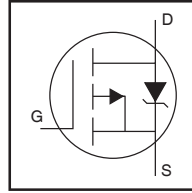


# AUIRF6218S AUIRF6218L

HEXFET® Power MOSFET

## Features

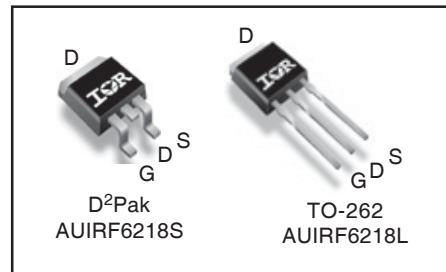
- Advanced Planar Technology
- Low On-Resistance
- P-Channel
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to T<sub>jmax</sub>
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



<b>V<sub>(BR)DSS</sub></b>	<b>-150V</b>
<b>R<sub>DS(on)</sub> max</b>	<b>150mΩ</b>
<b>I<sub>D</sub></b>	<b>-27A</b>

## Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T<sub>A</sub>) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V <sub>DS</sub>	Drain-to-Source Voltage	-150	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	-27	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	-19	
I <sub>DM</sub>	Pulsed Drain Current ①	-110	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	250	W
	Linear Derating Factor	1.6	W/°C
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ②	210	mJ
I <sub>AR</sub>	Avalanche Current ①	-16	A
dv/dt	Peak Diode Recovery dv/dt ③	8.2	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case ⑤	—	0.61	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (P CB Mounted, steady state) ⑥	—	40	

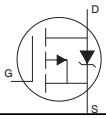
### Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-150	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.17	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	120	150	m $\Omega$	$V_{GS} = -10V, I_D = -16A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-3.0	—	-5.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	11	—	—	S	$V_{DS} = -50V, I_D = -16A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-25	$\mu A$	$V_{DS} = -120V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$

### Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	71	110	nC	$I_D = -16A$ $V_{DS} = -120V$ $V_{GS} = -10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	21	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	32	—		
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$V_{DD} = -75V$ $I_D = -16A$ $R_G = 3.9\Omega$ $V_{GS} = -10V$ ④
$t_r$	Rise Time	—	70	—		
$t_{d(off)}$	Turn-Off Delay Time	—	35	—		
$t_f$	Fall Time	—	30	—		
$C_{iss}$	Input Capacitance	—	2210	—	pF	$V_{GS} = 0V$ $V_{DS} = -25V$ $f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = -1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = -120V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V \text{ to } -120V$
$C_{oss}$	Output Capacitance	—	370	—		
$C_{rss}$	Reverse Transfer Capacitance	—	89	—		
$C_{oss}$	Output Capacitance	—	2220	—		
$C_{oss}$	Output Capacitance	—	170	—		
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	340	—		

### Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-27	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-110		
$V_{SD}$	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	150	—	ns	$T_J = 25^\circ\text{C}, I_F = -16A, V_{DD} = -25V$
$Q_{rr}$	Reverse Recovery Charge	—	860	—	nC	$di/dt = -100A/\mu s$ ③

#### Notes:

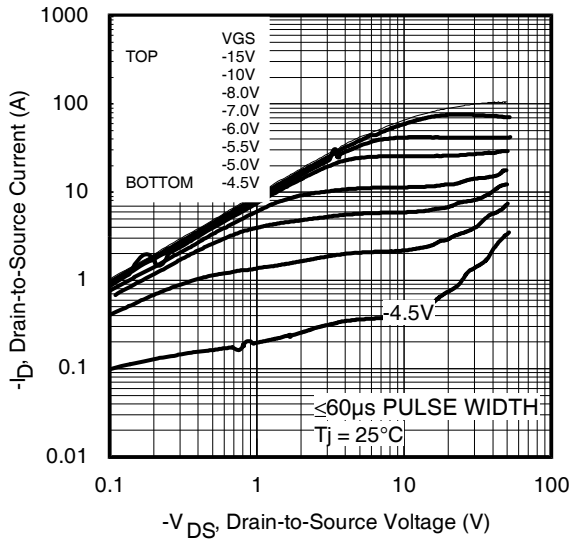
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1.6\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -17A$ .
- ③  $I_{SD} \leq -17A$ ,  $di/dt \leq -520A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑥ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

## Qualification Information<sup>†</sup>

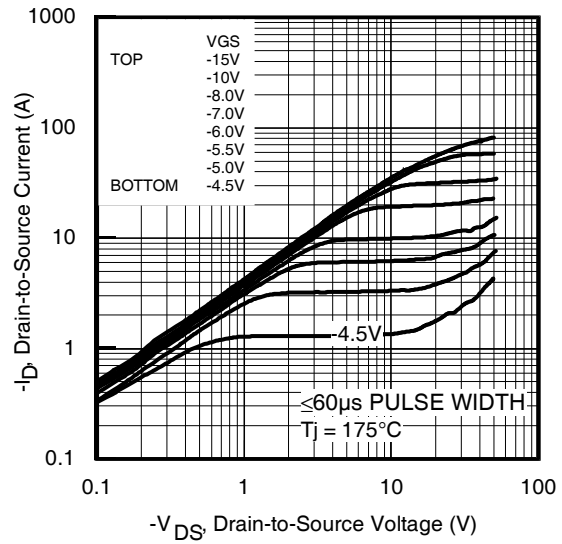
<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		TO-262	N/A
		D <sup>2</sup> Pak	MSL1
<b>ESD</b>	Machine Model	Class M4 (+/- 600V) <sup>††</sup> AEC-Q101-002	
	Human Body Model	Class H2 (+/- 3000V) <sup>††</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>††</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

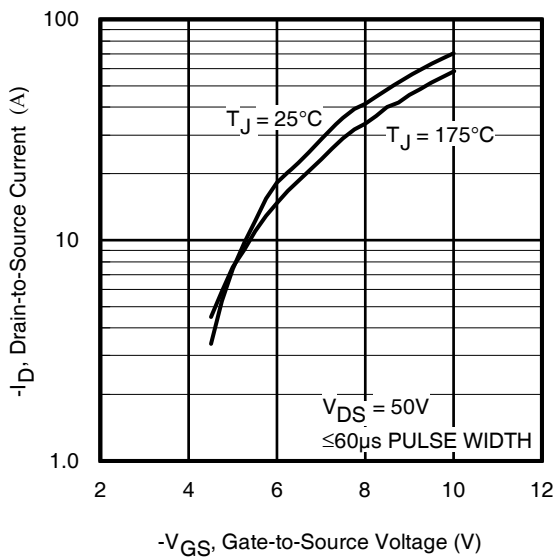
†† Highest passing voltage.



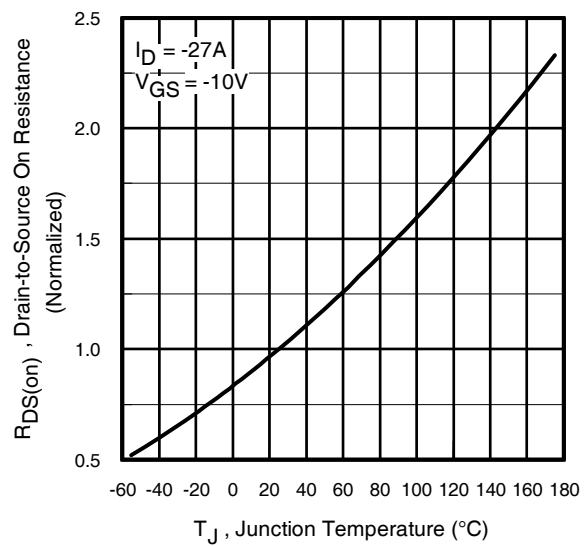
**Fig 1.** Typical Output Characteristics



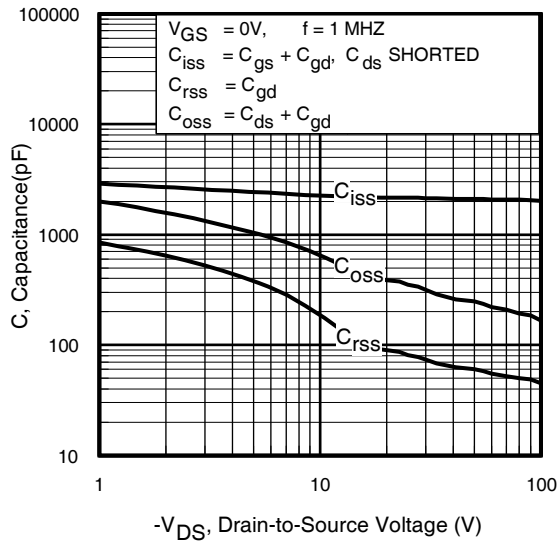
**Fig 2.** Typical Output Characteristics



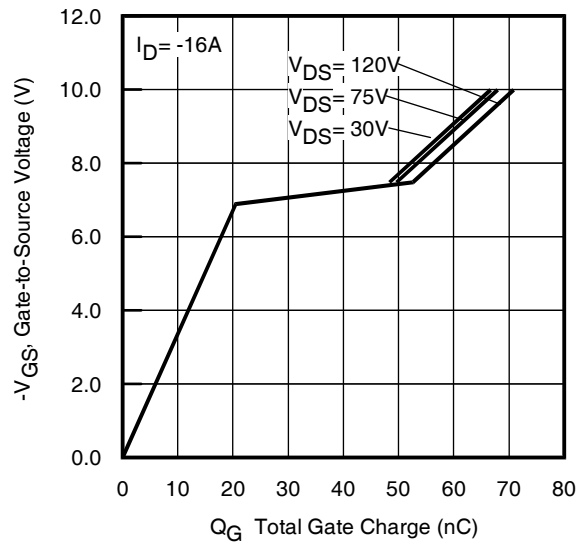
**Fig 3.** Typical Transfer Characteristics



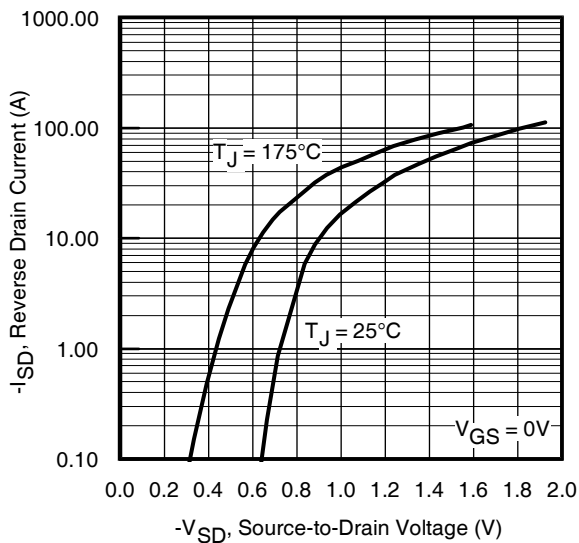
**Fig 4.** Normalized On-Resistance vs. Temperature



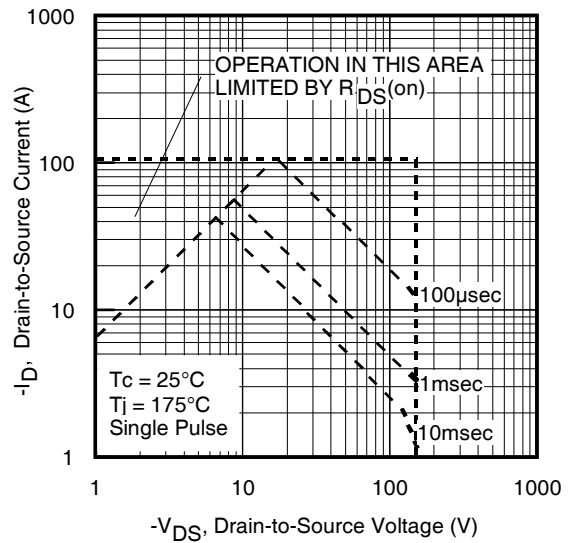
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



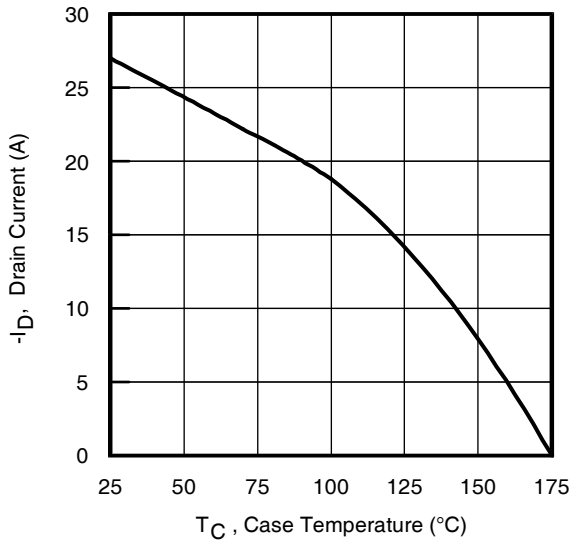
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



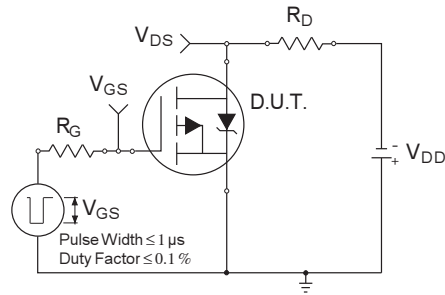
**Fig 7.** Typical Source-Drain Diode Forward Voltage



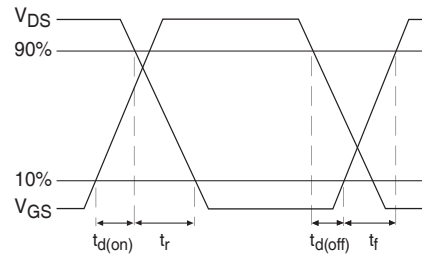
**Fig 8.** Maximum Safe Operating Area



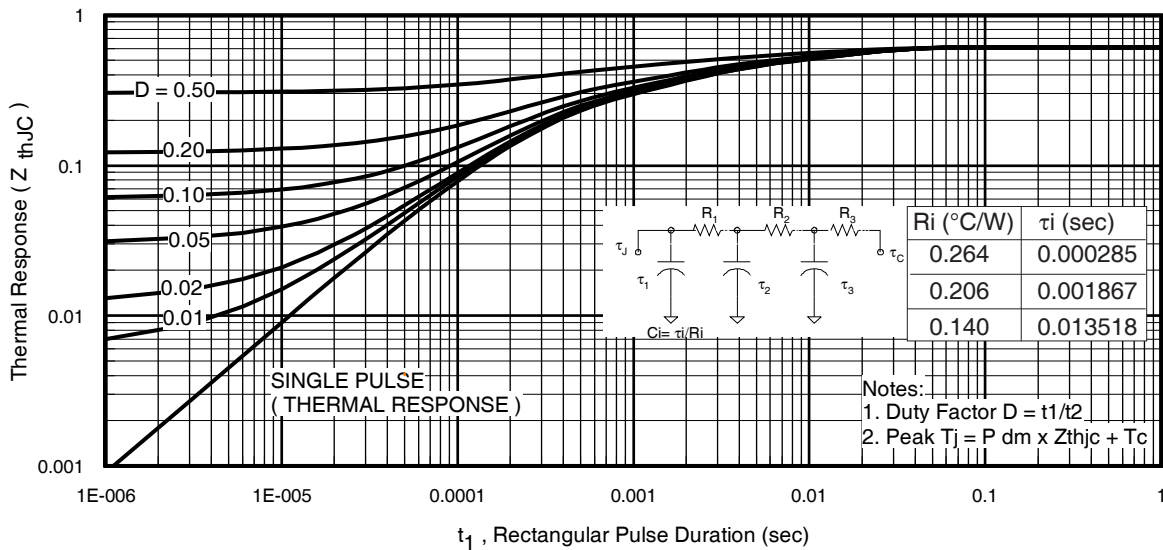
**Fig 9.** Maximum Drain Current vs. Ambient Temperature



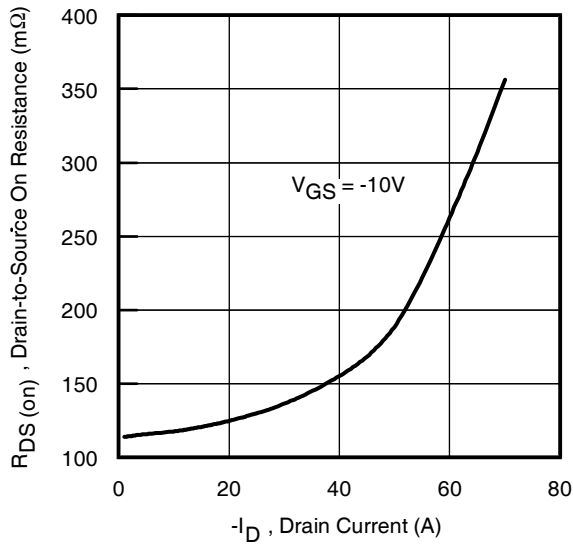
**Fig 10a.** Switching Time Test Circuit



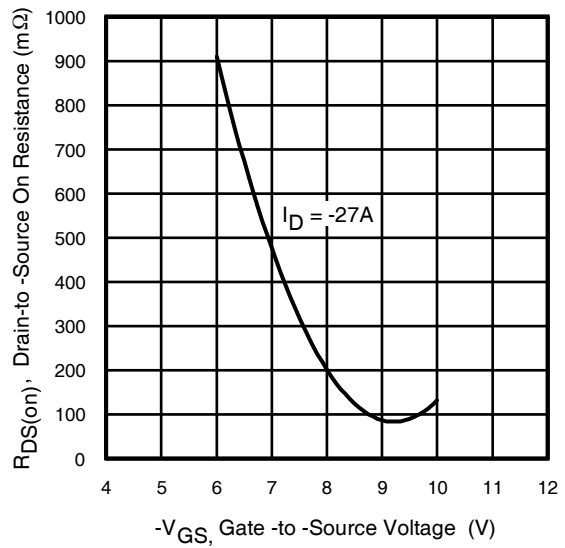
**Fig 10b.** Switching Time Waveforms



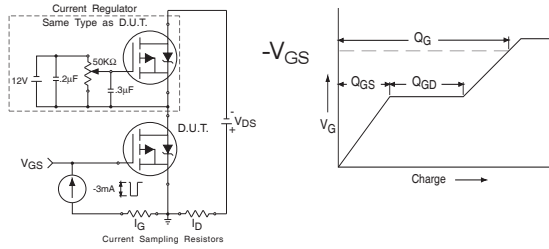
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



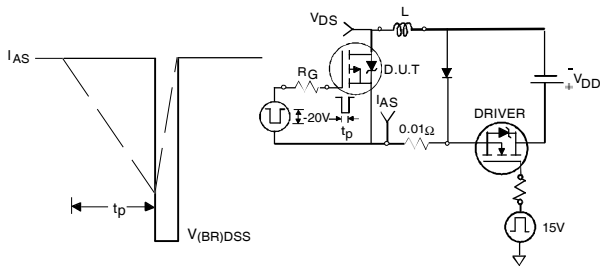
**Fig 12.** On-Resistance vs. Drain Current



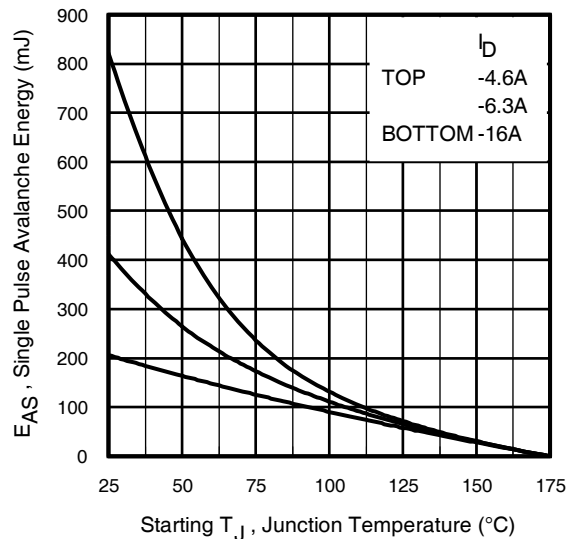
**Fig 13.** On-Resistance vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



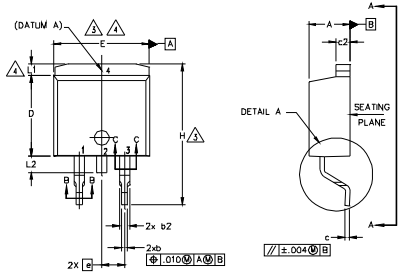
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



**Fig 15c.** Maximum Avalanche Energy vs. Drain Current

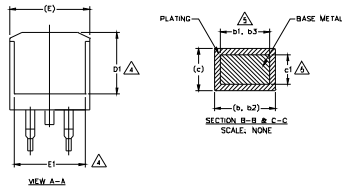
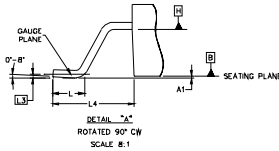
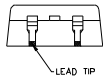
## D<sup>2</sup>Pak Package Outline

(Dimensions are shown in millimeters (inches))



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

**LEAD ASSIGNMENTS**

**HEXFET**

1. - GATE
- 2, 4. - DRAIN
3. - SOURCE

**IGBTs, CoPACK**

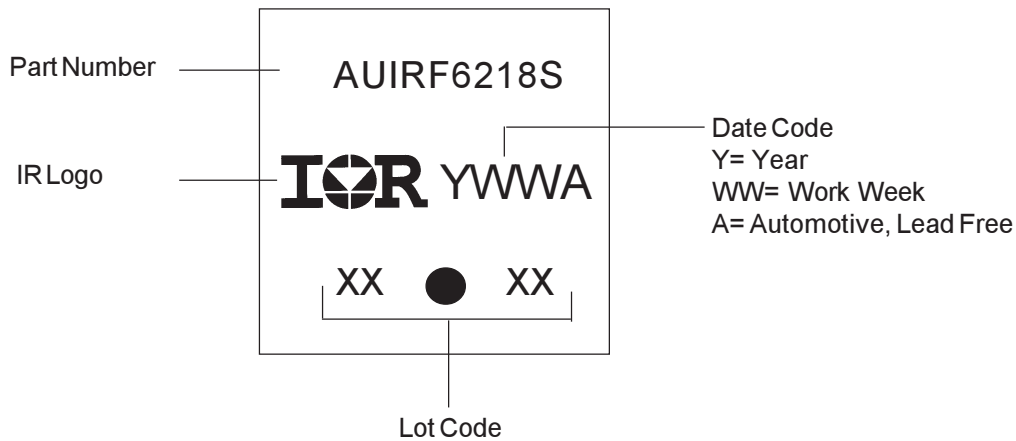
1. - GATE
- 2, 4. - COLLECTOR
3. - EMITTER

**DIODES**

1. - ANODE \*
- 2, 4. - CATHODE
3. - ANODE

\* PART DEPENDENT.

## D<sup>2</sup>Pak Part Marking Information

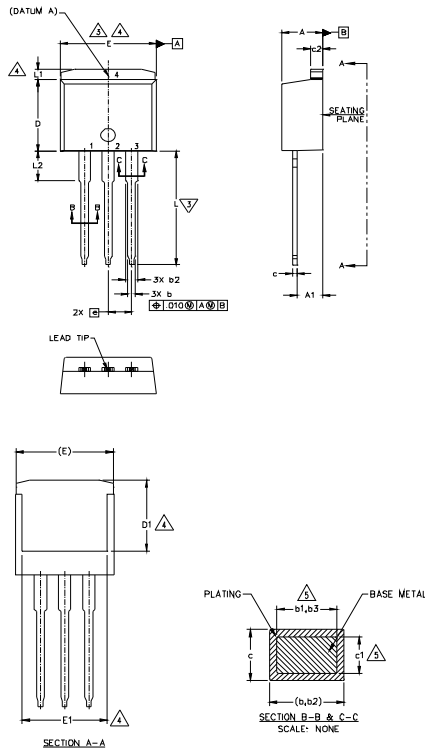


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	—	1.65	—	.065	4
L2	3.56	3.71	.140	.146	

NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994  
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)  
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (0.005) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.  
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION L, L1, D1 & E1.  
 5. DIMENSION L1 AND E1 APPLY TO BASE METAL ONLY.  
 6. CONTROLLING DIMENSION INCH.  
 7. — OUTLINE CONFORM TO ASIC TO-262 EXCEPT AS (max.), (min.) AND D1 (min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

LEAD ASSIGNMENTS

IRBTL: DIPACK

1- GATE  
 2- COLLECTOR  
 3- EMITTER  
 4- COLLECTOR

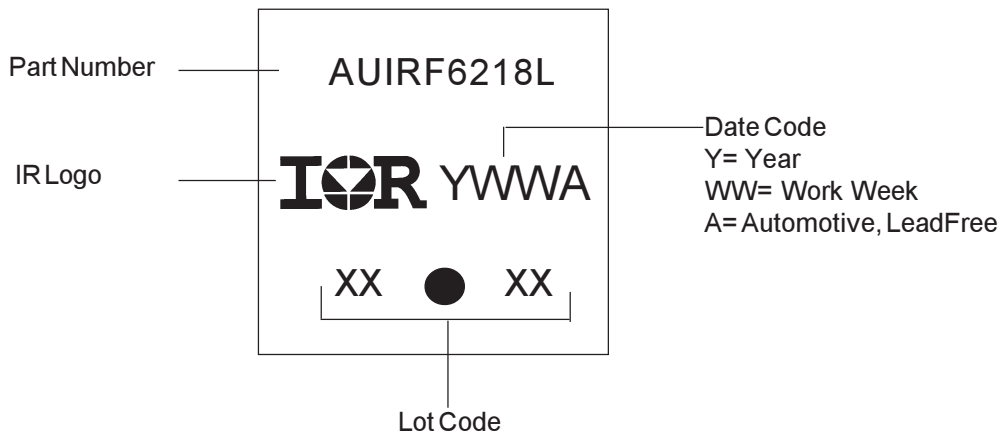
IRBEEF

1- GATE  
 2- DRINK  
 3- SOURCE  
 4- DRINK

DIODES

1- ANODE (TO DI) / OPEN (ON DI)  
 2- ANODE  
 3- ANODE  
 4- DRINK

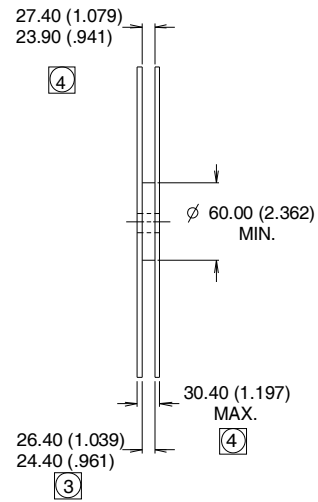
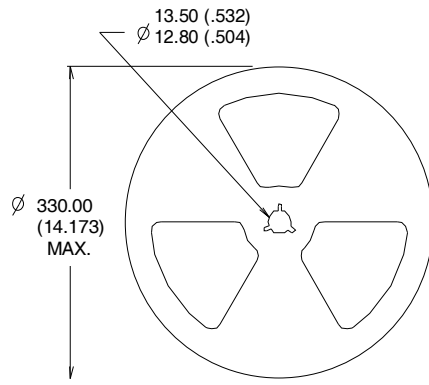
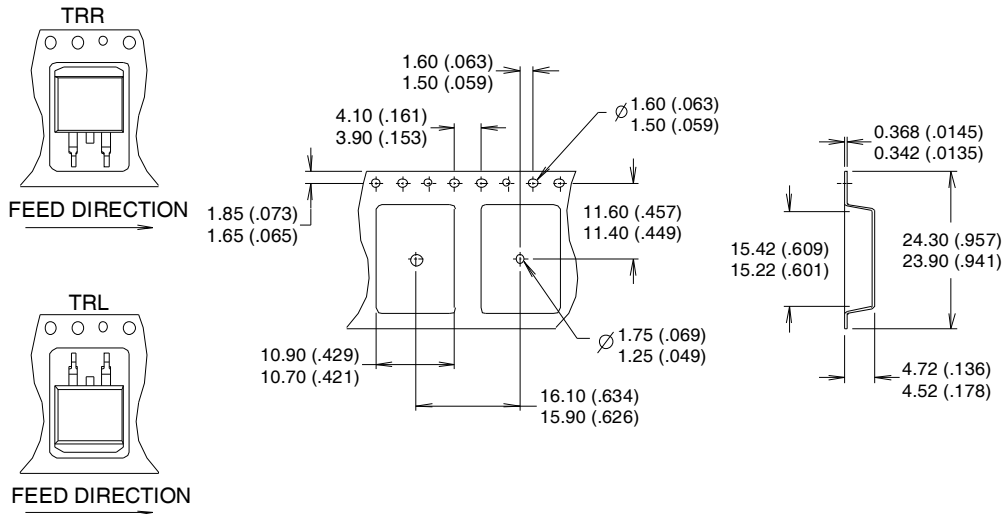
## TO-262 Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF6218L	TO-262	Tube	50	AUIRF6218L
AUIRF6218S	D2Pak	Tube	50	AUIRF6218S
		Tape and Reel Left	800	AUIRF6218STRL
		Tape and Reel Right	800	AUIRF6218STRR

## IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the "AU" prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR's terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

Only products certified as military grade by the Defense Logistics Agency (DLA) of the US Department of Defense, are designed and manufactured to meet DLA military specifications required by certain military, aerospace or other applications. Buyers acknowledge and agree that any use of IR products not certified by DLA as military-grade, in applications requiring military grade products, is solely at the Buyer's own risk and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR's Technical Assistance Center  
<http://www.irf.com/technical-info/>

### WORLD HEADQUARTERS:

101 N. Sepulveda Blvd., El Segundo, California 90245  
 Tel: (310) 252-7105